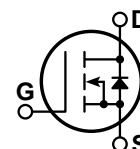
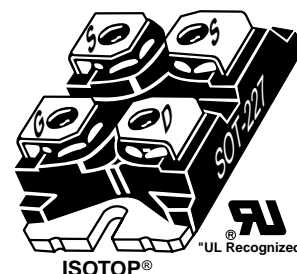


### POWER MOS 7™

**FREDFET**

Power MOS 7™ is a new generation of low loss, high voltage, N-Channel enhancement mode power MOSFETs. Both conduction and switching losses are addressed with Power MOS 7™ by significantly lowering  $R_{DS(ON)}$  and  $Q_g$ . Power MOS 7™ combines lower conduction and switching losses along with exceptionally fast switching speeds inherent with APT's patented metal gate structure.

- Lower Input Capacitance
- Lower Miller Capacitance
- Lower Gate Charge,  $Q_g$
- Increased Power Dissipation
- Easier To Drive
- Popular SOT-227 Package

**FAST RECOVERY BODY DIODE**


#### MAXIMUM RATINGS

All Ratings:  $T_C = 25^\circ\text{C}$  unless otherwise specified.

Symbol	Parameter	APT11058JFLL	UNIT
$V_{DSS}$	Drain-Source Voltage	1100	Volts
$I_D$	Continuous Drain Current @ $T_C = 25^\circ\text{C}$	18	Amps
$I_{DM}$	Pulsed Drain Current <sup>①</sup>	76	
$V_{GS}$	Gate-Source Voltage Continuous	$\pm 30$	Volts
$V_{GSM}$	Gate-Source Voltage Transient	$\pm 40$	
$P_D$	Total Power Dissipation @ $T_C = 25^\circ\text{C}$	463	Watts
	Linear Derating Factor	3.70	W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to 150	$^\circ\text{C}$
$T_L$	Lead Temperature: 0.063" from Case for 10 Sec.	300	
$I_{AR}$	Avalanche Current <sup>①</sup> (Repetitive and Non-Repetitive)	18	Amps
$E_{AR}$	Repetitive Avalanche Energy <sup>①</sup>	50	mJ
$E_{AS}$	Single Pulse Avalanche Energy <sup>④</sup>	2500	

#### STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
$BV_{DSS}$	Drain-Source Breakdown Voltage ( $V_{GS} = 0V, I_D = 250\mu A$ )	1100			Volts
$I_{D(on)}$	On State Drain Current <sup>②</sup> ( $V_{DS} > I_{D(on)} \times R_{DS(on)}$ Max, $V_{GS} = 10V$ )	18			Amps
$R_{DS(on)}$	Drain-Source On-State Resistance <sup>②</sup> ( $V_{GS} = 10V, 0.5 I_{D[Cont.]}$ )			0.580	Ohms
$I_{DSS}$	Zero Gate Voltage Drain Current ( $V_{DS} = V_{DSS}, V_{GS} = 0V$ )			250	$\mu A$
	Zero Gate Voltage Drain Current ( $V_{DS} = 0.8 V_{DSS}, V_{GS} = 0V, T_C = 125^\circ\text{C}$ )			1000	
$I_{GSS}$	Gate-Source Leakage Current ( $V_{GS} = \pm 30V, V_{DS} = 0V$ )			$\pm 100$	nA
$V_{GS(th)}$	Gate Threshold Voltage ( $V_{DS} = V_{GS}, I_D = 2.5mA$ )	3		5	Volts



**CAUTION:** These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

# DYNAMIC CHARACTERISTICS

APT11058JFLL

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
$C_{iss}$	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1 \text{ MHz}$		4700		pF
$C_{oss}$	Output Capacitance			710		
$C_{rss}$	Reverse Transfer Capacitance			134		
$Q_g$	Total Gate Charge <sup>③</sup>	$V_{GS} = 10V$ $V_{DD} = 0.5 V_{DSS}$ $I_D = I_D [\text{Cont.}] @ 25^\circ\text{C}$		172		nC
$Q_{gs}$	Gate-Source Charge			24		
$Q_{gd}$	Gate-Drain ("Miller") Charge			109		
$t_{d(on)}$	Turn-on Delay Time	$V_{GS} = 15V$ $V_{DD} = 0.5 V_{DSS}$ $I_D = I_D [\text{Cont.}] @ 25^\circ\text{C}$ $R_G = 0.6\Omega$		16		ns
$t_r$	Rise Time			8		
$t_{d(off)}$	Turn-off Delay Time			40		
$t_f$	Fall Time			12		

# SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
$I_S$	Continuous Source Current (Body Diode)			18	Amps
$I_{SM}$	Pulsed Source Current <sup>①</sup> (Body Diode)			76	
$V_{SD}$	Diode Forward Voltage <sup>②</sup> ( $V_{GS} = 0V$ , $I_S = -I_D [\text{Cont.}]$ )			1.3	Volts
$dv/dt$	Peak Diode Recovery $dv/dt$ <sup>⑤</sup>			18	V/ns
$t_{rr}$	Reverse Recovery Time ( $I_S = -I_D [\text{Cont.}]$ , $di/dt = 100A/\mu s$ )	$T_j = 25^\circ\text{C}$		300	ns
		$T_j = 125^\circ\text{C}$		600	
$Q_{rr}$	Reverse Recovery Charge ( $I_S = -I_D [\text{Cont.}]$ , $di/dt = 100A/\mu s$ )	$T_j = 25^\circ\text{C}$	1.7		$\mu\text{C}$
		$T_j = 125^\circ\text{C}$	4.47		
$I_{RRM}$	Peak Recovery Current ( $I_S = -I_D [\text{Cont.}]$ , $di/dt = 100A/\mu s$ )	$T_j = 25^\circ\text{C}$	11.4		Amps
		$T_j = 125^\circ\text{C}$	16.4		

# THERMAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case			0.27	$^\circ\text{C/W}$
$R_{\theta JA}$	Junction to Ambient			40	

① Repetitive Rating: Pulse width limited by maximum junction temperature.

② Pulse Test: Pulse width < 380  $\mu s$ , Duty Cycle < 2%

③ See MIL-STD-750 Method 3471

④ Starting  $T_j = +25^\circ\text{C}$ ,  $L = 15.43\text{mH}$ ,  $R_G = 25\Omega$ , Peak  $I_L = 18A$

⑤  $dv/dt$  numbers reflect the limitations of the test circuit rather than the device itself.  $I_S \leq -I_D [\text{Cont.}]$   $di/dt \leq 700A/\mu s$   $V_R \leq V_{DSS}$   $T_j \leq 150^\circ\text{C}$

APT Reserves the right to change, without notice, the specifications and information contained herein.

# SOT-227 (ISOTOP®) Package Outline

